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Nicole Barrese Accoll Bowene 12/13/04

Name of Person Making Deposit With United States Postal Service

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE							
In re application of: Huilong Zhu, et al.	Date: December 13, 2004						
Serial Number: 10/709,239	Examiner:						
Filed: 4/23/2004	Group Art Unit: 2811						

Title: STRUCTURES AND METHODS FOR MANUFACTURING OF DISLOCATION FREE STRESSED CHANNELS IN BULK SILICON AND 2070 Route 52

SOI CMOS DEVICES BY GATE STRESS ENGINEERING WITH SIGE AND/OR Si:C 2070 Route 52 Hopewell Junction, NY 12533-6531

Signature of Person Making Deposit

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

Pursuant to the duty of disclosure set forth in 37 C.F.R. 1.56, and further pursuant to the provisions of 37 C.F.R. 1.97 and 1.98, applicants hereby respectfully submit copies of the non-US patents and publications as listed on Form PTO-1449, attached hereto.

In citing these documents, no representation is made nor intended as to the pertinency or non-pertinency of the art, that better art than that listed is not available, or that other art is not applicable.

No fee is believed to be due for this submission. If any fees are required, however, the Commissioner is hereby authorized to charge such fees to Deposit Account No. 09-0458.

Respectfully submitted,

Huilong Zhu, et al.

Joseph P. Abate

Registration No. 30,238

Telephone: (845) 894-4633

FIS920030375

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FORM PTO-1	1449 (Modified)	٠, ٠,	ATTY. DOCKET NO F1S920030375	SERIAL NO.					
	ENTS AND PUBLICA S INFORMATION DIS	CI/OSIBE	Cor, Corner	APPLICANT: H	uilong	<u> 10/709,</u> Zhu, et			
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REFERENCE I	DESIGNATION	U.S.	PATE	NT DOCUMENTS					
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		49 (Modified)			ATTY. DOCKET NO. SERIAL NO. 10/709,239					
	ГS	NTS AND PUBLICA INFORMATION DIS			APPLICANT: Hu	ilong Z	hu,	, et al.		
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation is not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449 (Modified)
LIST OF PATENTS AND PUBLICATIONS
FOR APPLICANT'S INFORMATION
DISCLOSURE STATEMENT

Docket Number (Optional) FIS920030375	Application Number 10/709,239				
Applicant(s) Huilong Zhu, et al.	A CONTRACTOR OF THE CONTRACTOR				
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